

MOSFET
Product Summary

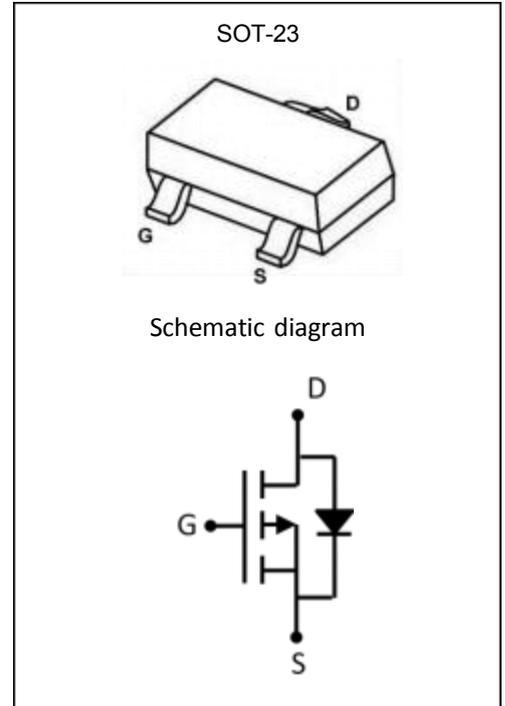
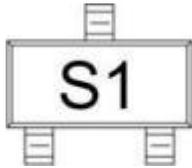
V _{(BR)DSS}	R _{DS(on)MAX}	I _D
-20V	110mΩ@-4.5V	-2.3A
	140mΩ@-2.5V	

Feature

- TrenchFET Power MOSFET
- Excellent R_{DS(on)} and Low Gate Charge

Application

- DC/DC Converter
- Load Switch for Portable Devices
- Battery Switch

MARKING:

ABSOLUTE MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V _{DS}	-20	V
Gate-Source Voltage	V _{GS}	±8	V
Continuous Drain Current	I _D	-2.3	A
Pulsed Drain Current (t=300μs)	I _{DM}	-10	A
Power Dissipation	P _D	0.35	W
Thermal Resistance from Junction to Ambient	R _{θJA}	357	°C/W
Junction Temperature	T _J	150	°C
Storage Temperature	T _{STG}	-55~ +150	°C

MOSFET ELECTRICAL CHARACTERISTICS(T_a=25°C unless otherwise noted)

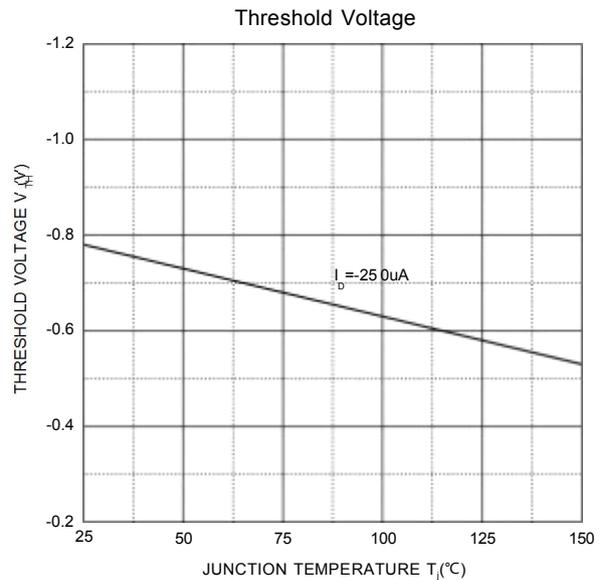
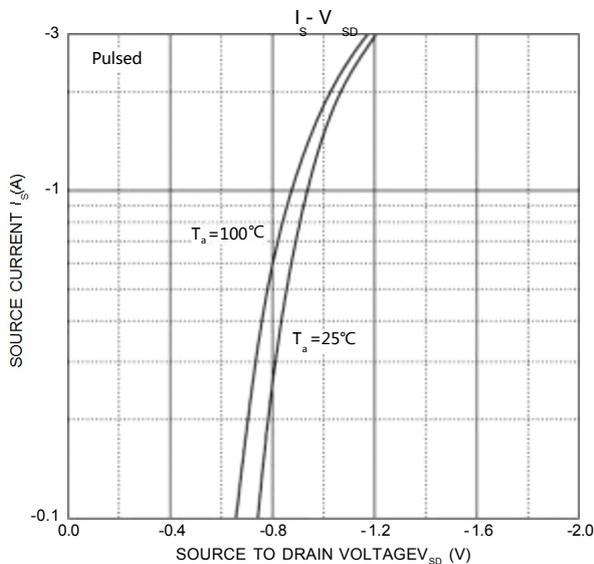
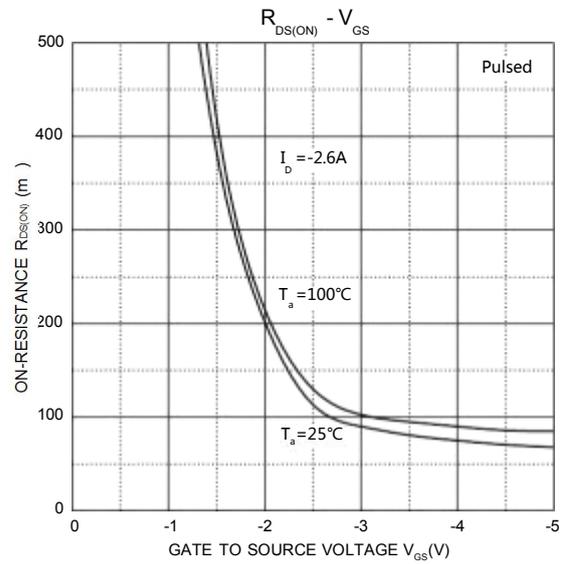
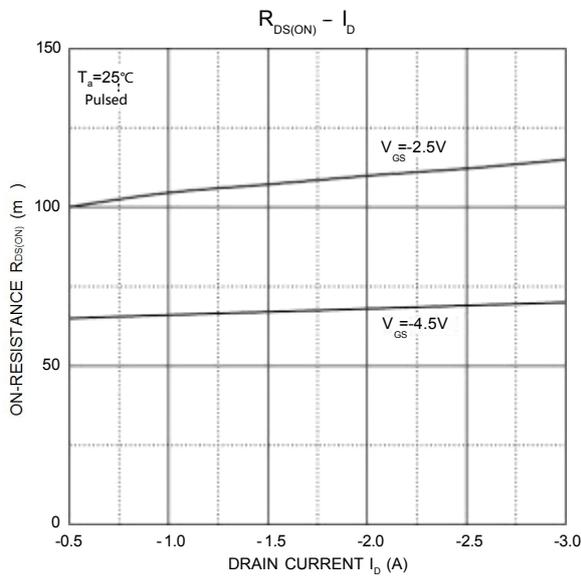
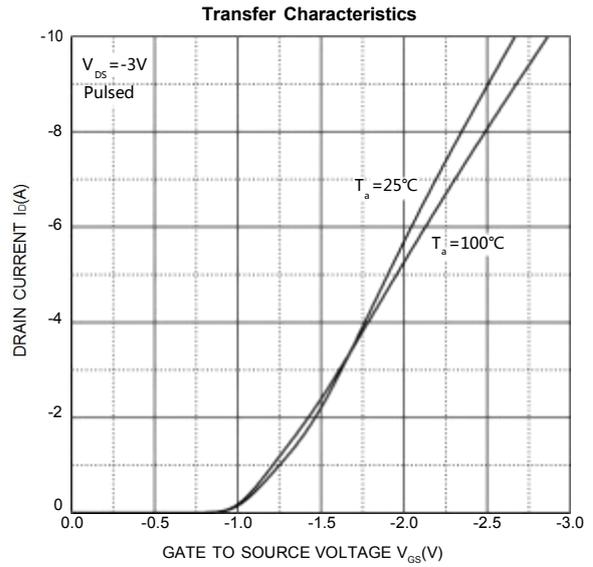
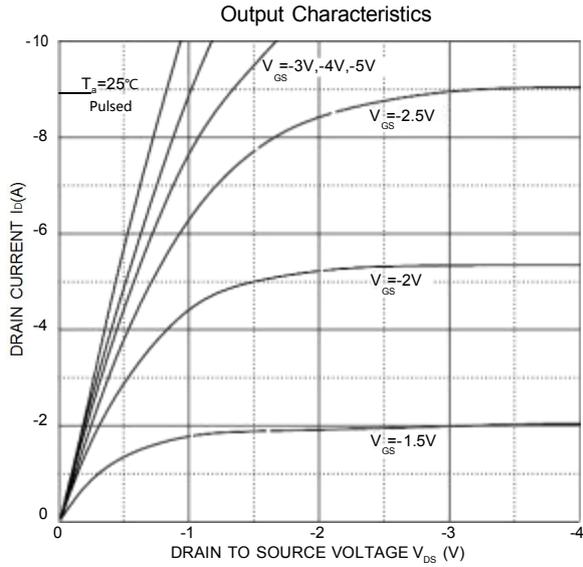
Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = -250μA	-20			V
Zero gate voltage drain current	I _{DSS}	V _{DS} = -20V, V _{GS} = 0V			-1	μA
Gate-body leakage current	I _{GSS}	V _{GS} = ±8V, V _{DS} = 0V			±100	nA
Gate threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250μA	-0.4	-0.7	-1	V
Drain-source on-resistance ^a	R _{DS(on)}	V _{GS} = -4.5V, I _D = -3A		70	110	mΩ
		V _{GS} = -2.5V, I _D = -2A		110	140	
Forward tranconductance ^a	g _{FS}	V _{DS} = -5V, I _D = -2A	5			S
Dynamic characteristics^b						
Input Capacitance	C _{iss}	V _{DS} = -10V, V _{GS} = 0V, f = 1MHz		405		pF
Output Capacitance	C _{oss}			75		
Reverse Transfer Capacitance	C _{rss}			55		
Gate resistance	R _g	f = 1MHz		6		Ω
Total Gate Charge	Q _g	V _{DS} = -10V, V _{GS} = -2.5V, I _D = -3A		3.3	12	nC
Gate-Source Charge	Q _{gs}			0.7		
Gate-Drain Charge	Q _{gd}			1.3		
Turn-on delay time	t _{d(on)}	V _{DD} = -10V, V _{GEN} = -4.5V, I _D = -1A R _L = 10Ω, R _{GEN} = 1Ω		11		ns
Turn-on rise time	t _r			35		
Turn-off delay time	t _{d(off)}			30		
Turn-off fall time	t _f			10		
Source-Drain Diode characteristics						
Diode forward current	I _s	T _c = 25°C			-2.3	A
Diode pulsed forward current ^a	I _{SM}				-10	A
Diode Forward voltage	V _{DS}	V _{GS} = 0V, I _s = -1.3A			-1.2	V

Notes :

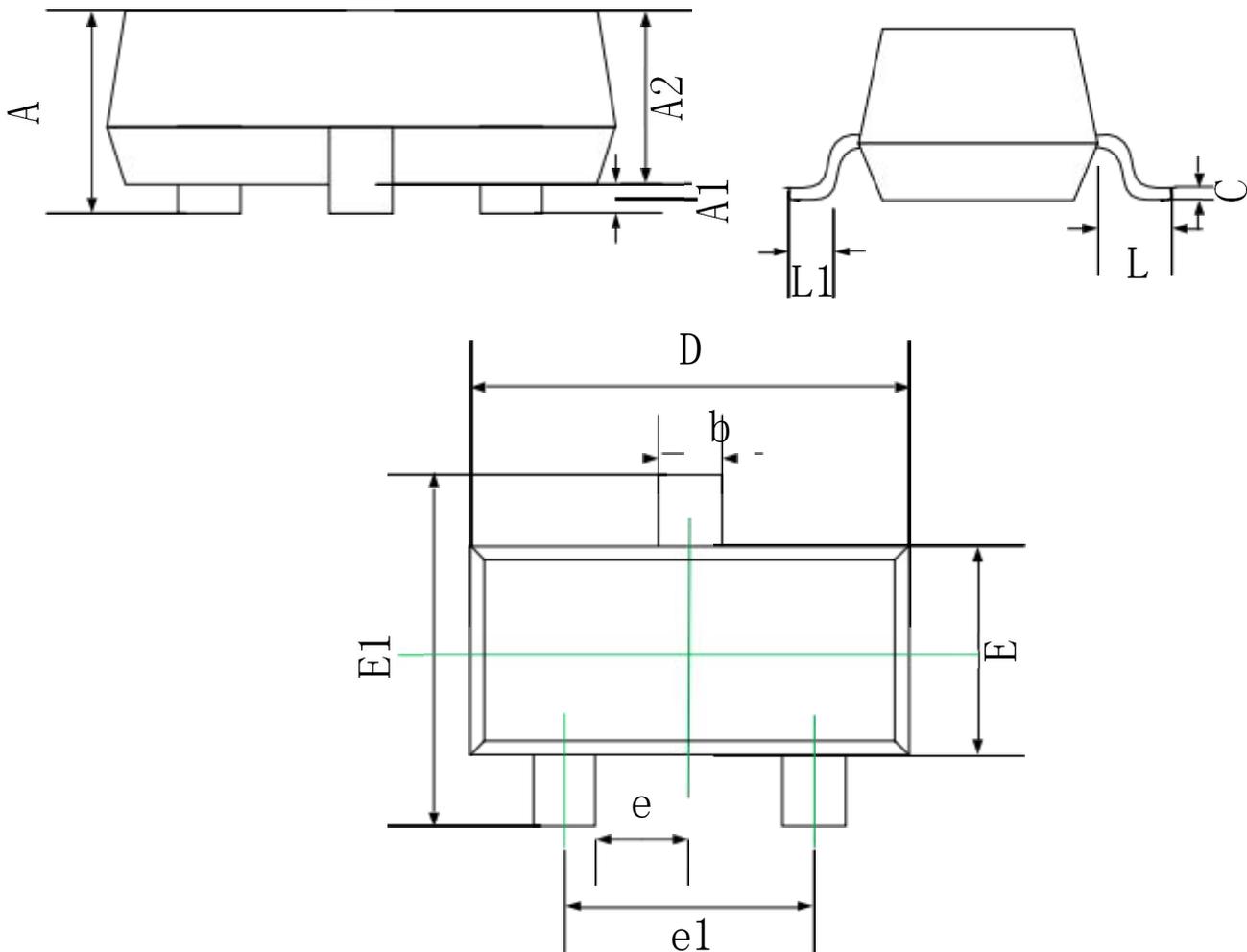
a. Pulse Test : Pulse Width < 300μs, Duty Cycle ≤ 2%.

b. Guaranteed by design, not subject to production testing.

Typical Electrical and Thermal Characteristics



SOT-23 Package Information

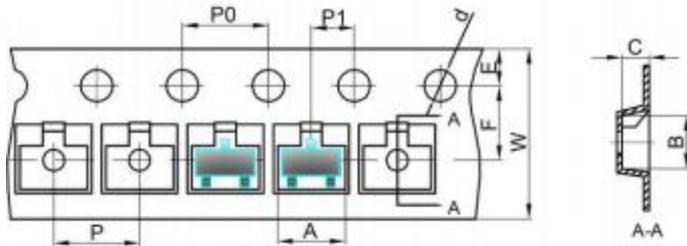


Symbol	Dimensions In Millimeters	
	Min.	Max.
A	0.90	1.15
A1	0.00	0.10
A2	0.90	1.05
b	0.30	0.50
c	0.08	0.15
D	2.80	3.00
E	1.20	1.40
E1	2.25	2.55
e	0.95 REF.	
e1	1.80	2.00
L	0.55 REF.	
L1	0.30	0.50

SOT-23 Tape and Reel

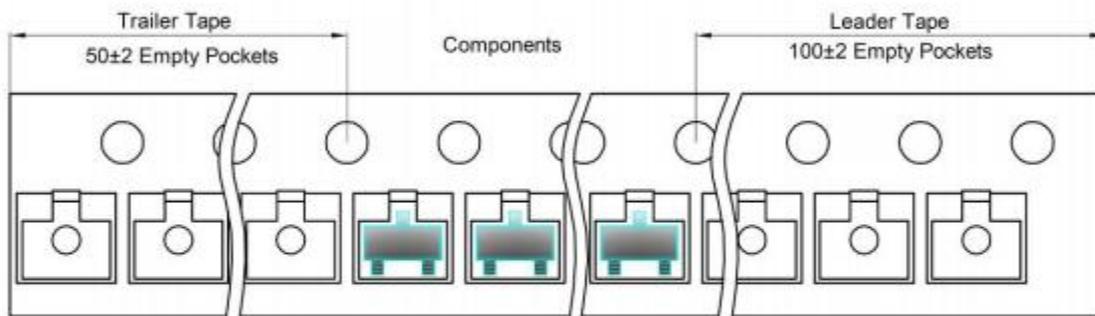
SOT-23 Tape and reel

SOT-23 Embossed Carrier Tape

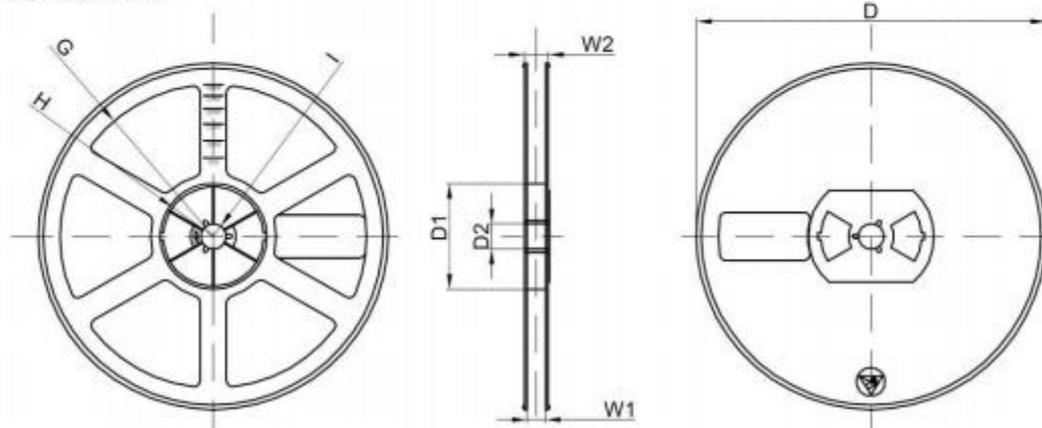


Dimensions are in millimeter										
Pkg type	A	B	C	d	E	F	P0	P	P1	W
SOT-23	3.15	2.77	1.22	Ø1.50	1.75	3.50	4.00	4.00	2.00	8.00

SOT-23 Tape Leader and Trailer



SOT-23 Reel



Dimensions are in millimeter								
Reel Option	D	D1	D2	G	H	I	W1	W2
7" Dia	Ø178.00	54.40	13.00	R78.00	R25.60	R6.50	9.50	12.30

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
3000 pcs	7 inch	30,000 pcs	203×203×195	120,000 pcs	438×438×220	

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